

P-Channel Enhancement-Mode MOSFET “FETlington”

DESIGNED FOR:

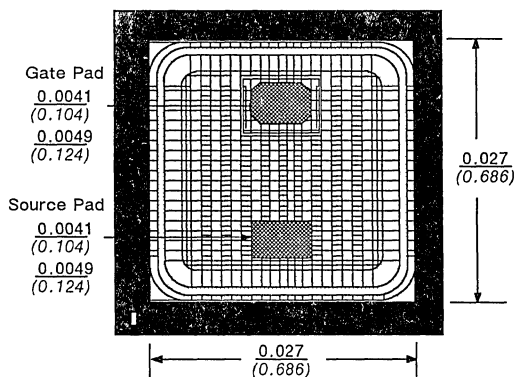
- Switching (P-Channel Complement to 2N7000)

FEATURES

- Low $r_{DS(on)} < 10 \Omega$
- Available in Surface Mount

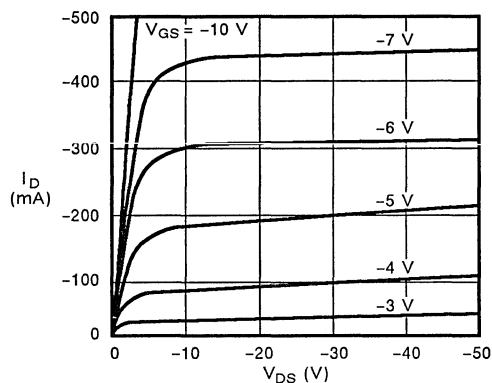
TYPE	PACKAGE	DEVICE
Single	TO-206AC	• VP0610E, TP0610E
	TO-92	• VP0610L, TP0610L
	SOT-23	• VP0610T, TP0610T
	14-Pin Plastic	• VQ2000J
	14-Pin Dual-In-Line	• VQ2000P
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

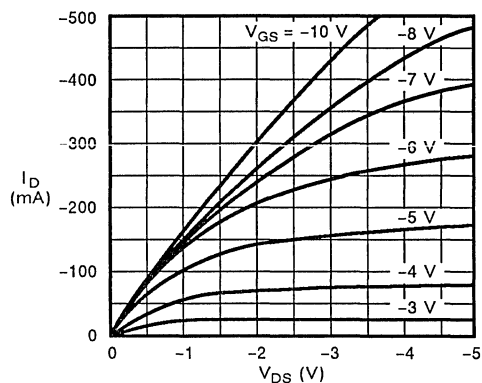


TYPICAL CHARACTERISTICS

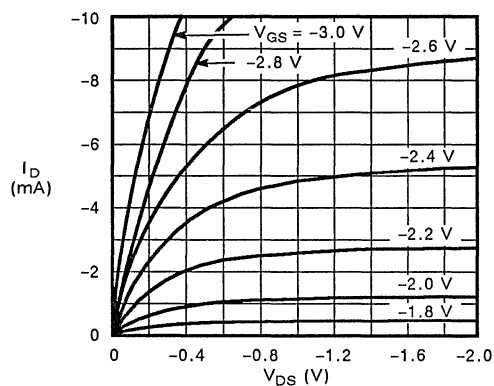
Output Characteristics



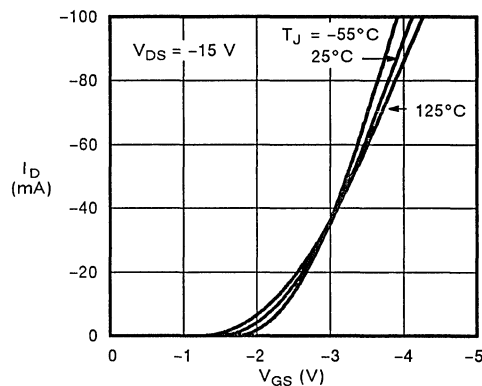
Ohmic Region Characteristics



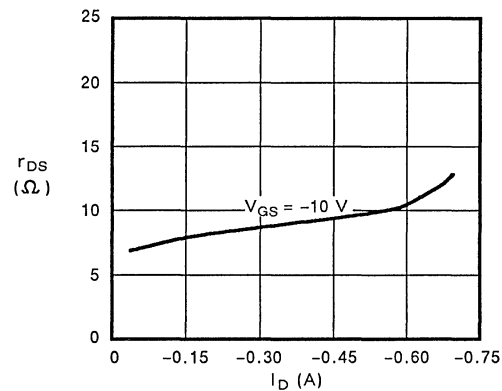
Output Characteristics for Low Gate Drive



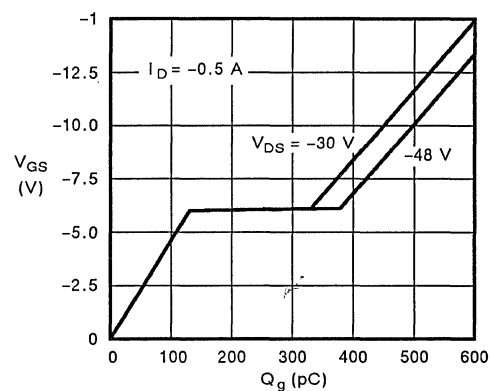
Transfer Characteristics



On-Resistance

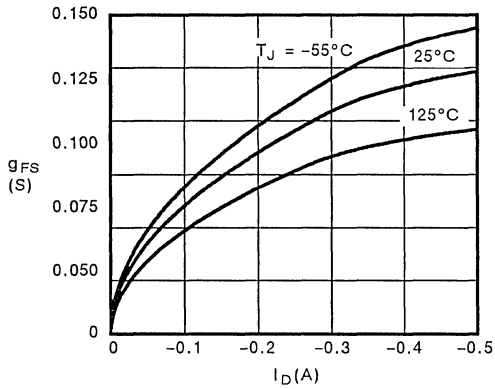


Gate Charge

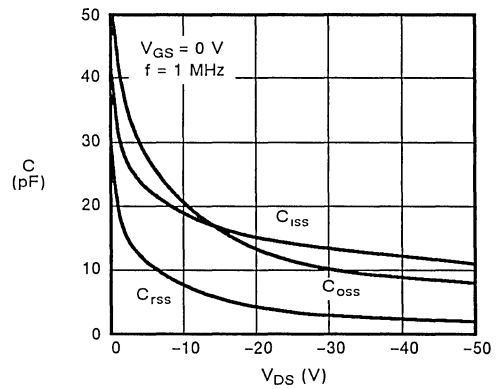


TYPICAL CHARACTERISTICS

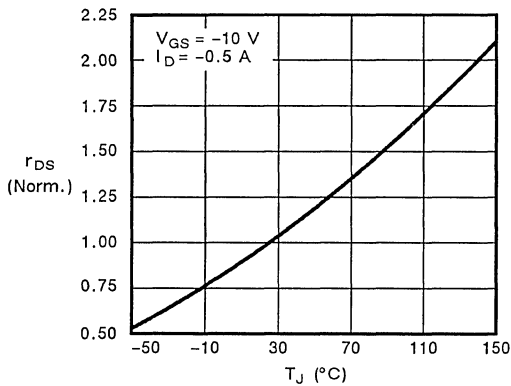
Transconductance



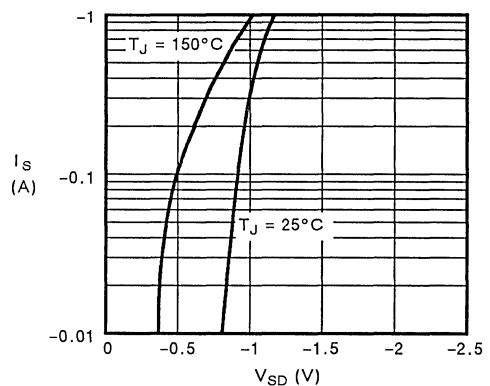
Capacitance



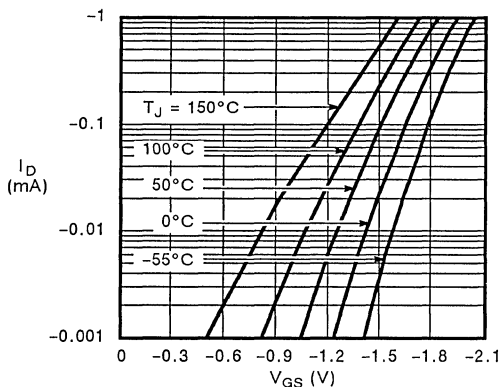
On-Resistance vs. Junction Temperature



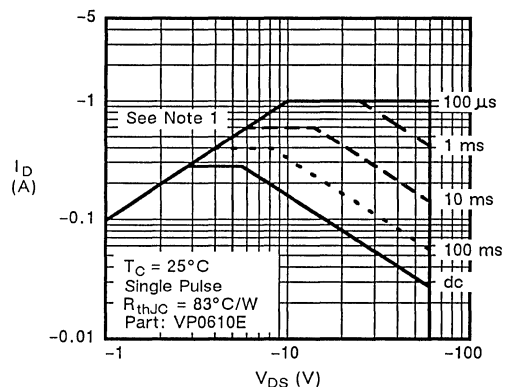
Source-Drain Diode Forward Voltage



Threshold Region



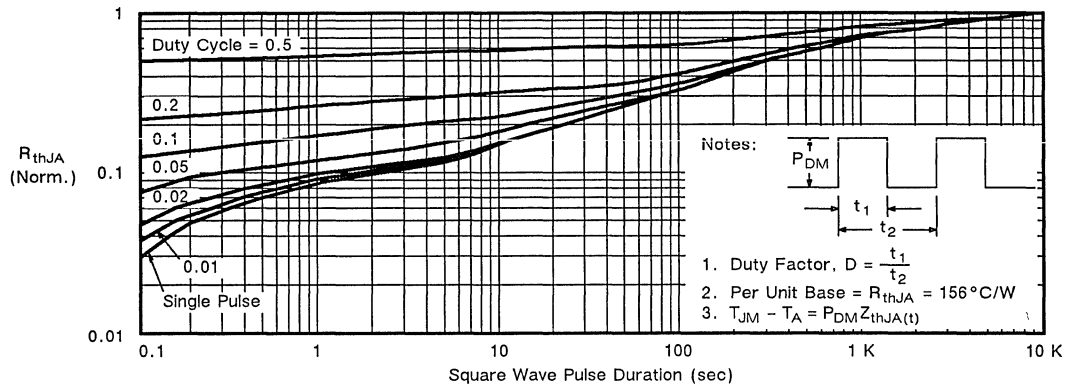
Safe Operating Area



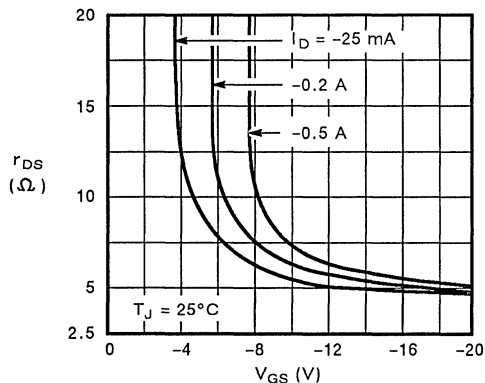
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

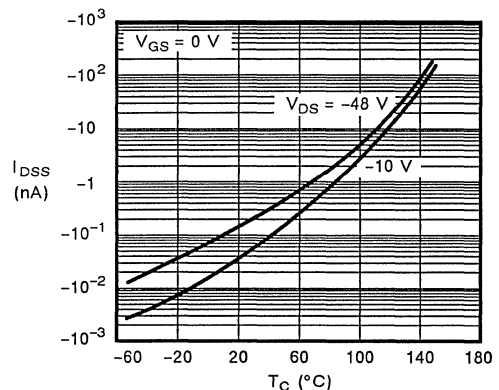
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



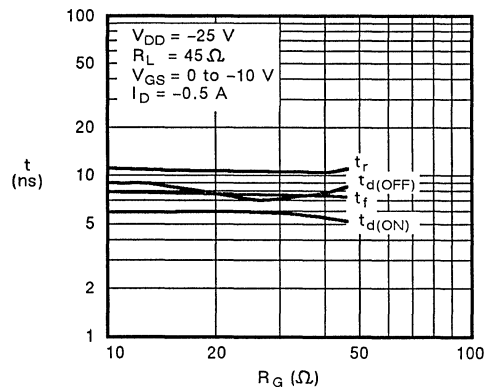
On-Resistance vs. Gate to Source Voltage



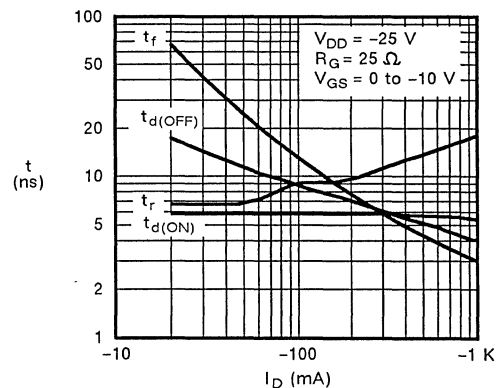
Off State Current



Drive Resistance Effects on Switching

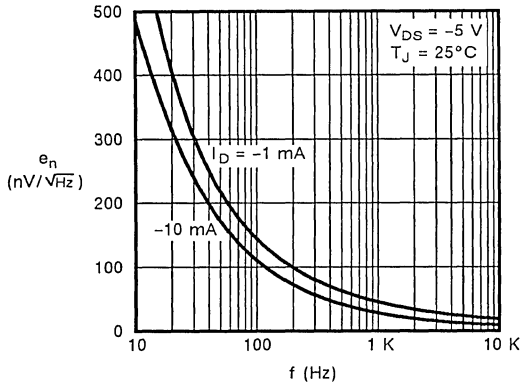


Load Condition Effects on Switching

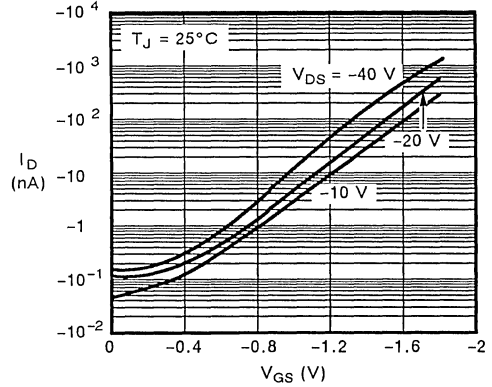


TYPICAL CHARACTERISTICS

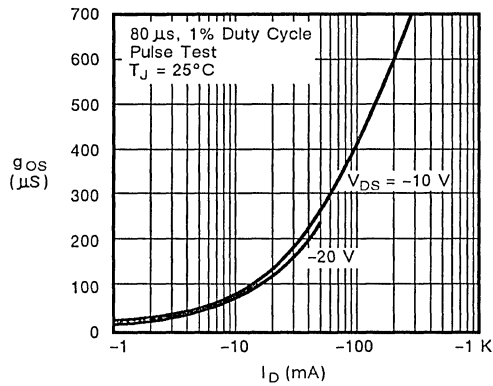
Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-206AC)

